

Rapid Thermal Annealing
 Rapid Thermal Oxidation
 Ohmic Contact Annealing
 Implant Annealing
 RTCVD of Graphene & hBN
 Selenization
 Silicon Carbonization
 Crystallization
 Densification



AS-Micro

3-inch RTP System for Laboratories

- From room temperature up to 1250°C
- Fast ramp rates up to 250°C/s
- Standard vacuum and gas mixing capabilities
- Twin chamber version to avoid cross contamination



AS-One

Versatile RTP Systems 100mm (4") and 150mm (6")

- Floor standing system, reduced footprint
- From room temperature up to 1450°C
- Cold wall chamber technology
- Gas mixing and high vacuum capabilities
- Pulse Annealing
- Optional: turbo pump, fast cooling system



AS-Premium

Multi-Configuration RTP system for substrates up to 156x156mm²

- Top or both side heating
- Multi-zone lamp furnace
- From room temperature up to 1250°C
- Manual or robot loading
- Cold wall chamber technology
- High vacuum capability
- Up to 8 process gas lines with MFC
- Optional: turbo pump, fast cooling system



AS-Master

200mm RTP System from R&D to Production

- Multi-zone lamp furnace
- From room temperature up to 1450°C
- Manual or robot loading
- Cold wall chamber technology
- High vacuum capability
- Up to 8 process gas lines with MFC
- Optional: turbo pump, fast cooling system



Zenith-Series

High Temperature RTP system

- Substrates up to 200mm diameter
- Process temperature from 450-2000°C
- Low inertia tungsten heating elements
- High vacuum system with turbo pump
- Graphene and silicon carbide applications



APPLICATIONS

Microelectronics
Power Devices
Optoelectronics
Sensors
MEMS
Solar cells
R&D



JETLIGHT

Entry-level Batch-Type Rapid Thermal Annealing Furnace

- From room temperature up to 1000°C
- Thermocouple temperature control
- Fast ramp rates up to 200°C/s
- Substrate size up to 50mm diameter
- Up to 2 process gas lines with MFC



JETFIRST 100-200

Bench-top Rapid Thermal Process Furnace up to 200mm

- Bench-top system, reduced footprint
- From room temperature up to 1300°C
- Fast ramp rates up to 200°C/s
- Cold-wall design for process reproducibility
- Substrate size up to 200mm diameter
- Up to 4 process gas lines with MFC



JETFIRST 300

Rapid Thermal Process Furnace up to 300mm

- Floor standing system, reduced footprint
- From room temperature up to 1200°C
- Fast ramp rates up to 150°C/s
- Substrate size up to 300mm diameter
- One purge gas line
- Up to 4 process gas lines with MFC
- Digital PID temperature controller

The cold wall chamber technology and the extended temperature range of Rapid Thermal Processing associated with optimized susceptors allows processing of a wide range of substrates:

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|--------------------------------|------------------|
| Silicon wafers | Glass substrates |
| Compound semiconductor wafers | Metals |
| GaN, SiC, InP, GaAs, Ge & more | Polymers |
| Poly silicon wafers | |

ABOUT ANNEALSYS

Provider of innovative solutions for Rapid Thermal Processing (RTP) and Chemical Vapor Deposition (CVD/ALD) systems, dedicated to R&D and production.

Headquartered in Montpellier, France, we provide outstanding technical and process customer support through a global sales and service network.

